

# NCE N-Channel Enhancement Mode Power MOSFET



## Package Marking and Ordering Information

| Device Marking  | Device  | Device Package | Reel Size | Tape width | Quantity   |
|-----------------|---------|----------------|-----------|------------|------------|
| 6004 <b>*</b> * | NCE6004 | SOT-23         | Ø180mm    | 8 mm       | 3000 units |

## Absolute Maximum Ratings (T<sub>A</sub>=25℃unless otherwise noted)

| Parameter  | Symbol                           | Limit      | Unit |  |
|--|----------------------------------|------------|------|--|
| Drain-Source Voltage                             | VDS                              | 60         | V    |  |
| Gate-Source Voltage                              | VGS                              | ±20        | V    |  |
| Drain Current-Continuous                         | ID                               | 4          | А    |  |
| Drain Current-Pulsed (Note 1)                    | IDM                              | 16         | А    |  |
| Single pulse avalanche energy (Note 5)           | E <sub>AS</sub>                  | 36         | mJ   |  |
| Maximum Power Dissipation                        | PD                               | 1.7        | W    |  |
| Operating Junction and Storage Temperature Range | T <sub>J</sub> ,T <sub>STG</sub> | -55 To 150 | °C   |  |

## **Thermal Characteristic**

| Thermal Resistance, Junction-to-Ambient (Note 2) | R <sub>θJA</sub> | 73.5 | °C/W |  |
|--|------------------|------|------|--|
| Thermal Resistance, Junction-to-Case (Note 2)    | Rejc             | 55   | °C/W |  |



#### Electrical Characteristics (T<sub>A</sub>=25<sup>°</sup>Cunless otherwise noted)

| Parameter                          | Symbol              | Condition   | Min | Тур  | Max  | Unit |
|------------------------------------|---------------------|---|-----|------|------|------|
| Off Characteristics                | I                   |   |     |      |      |      |
| Drain-Source Breakdown Voltage     | BV <sub>DSS</sub>   | V <sub>GS</sub> =0V I <sub>D</sub> =250µA               | 60  | -    | -    | V    |
| Zero Gate Voltage Drain Current    | IDSS                | V <sub>DS</sub> =60V,V <sub>GS</sub> =0V                | -   | -    | 1    | μA   |
| Gate-Body Leakage Current          | Igss                | V <sub>GS</sub> =±20V,V <sub>DS</sub> =0V               | -   | -    | ±100 | nA   |
| On Characteristics (Note 3)        |                     |   |     |      |      | 1    |
| Gate Threshold Voltage             | V <sub>GS(th)</sub> | V <sub>DS</sub> =V <sub>GS</sub> ,I <sub>D</sub> =250µA | 1.2 | 1.8  | 2.5  | V    |
| Drain-Source On-State Resistance   | <u> </u>            | V <sub>GS</sub> =10V, I <sub>D</sub> =4A                | -   | 38   | 50   | mΩ   |
|                                    | R <sub>DS(ON)</sub> | V <sub>GS</sub> =4.5V, I <sub>D</sub> =4A               | -   | 58   | 80   | mΩ   |
| Forward Transconductance           | <b>g</b> fs         | V <sub>DS</sub> =5V,I <sub>D</sub> =4A                  | -   | 3    | -    | S    |
| Dynamic Characteristics (Note4)    |                     |   |     |      | L    | 1    |
| Input Capacitance                  | Clss                | V <sub>DS</sub> =30V,V <sub>GS</sub> =0V,               | -   | 553  | -    | pF   |
| Output Capacitance                 | Coss                |   | -   | 43   | -    | pF   |
| Reverse Transfer Capacitance       | Crss                | F=1.0MHz  | -   | 37   | -    | pF   |
| Switching Characteristics (Note 4) | L                   |   |     |      |      |      |
| Turn-on Delay Time                 | t <sub>d(on)</sub>  |   | -   | 6    | -    | nS   |
| Turn-on Rise Time                  | tr                  | V <sub>DD</sub> =30V,I <sub>D</sub> =4A                 | -   | 11   | -    | nS   |
| Turn-Off Delay Time                | t <sub>d(off)</sub> | $V_{GS}$ =10V, $R_{GEN}$ =1 $\Omega$                    | -   | 18   | -    | nS   |
| Turn-Off Fall Time                 | t <sub>f</sub>      |   | -   | 10   | -    | nS   |
| Total Gate Charge                  | Qg                  |   | -   | 11.4 | -    | nC   |
| Gate-Source Charge                 | Q <sub>gs</sub>     | $V_{DS}$ =30V,I <sub>D</sub> =4A,                       | -   | 1.7  | -    | nC   |
| Gate-Drain Charge                  | Q <sub>gd</sub>     | V <sub>GS</sub> =10V                                    | -   | 2.6  | -    | nC   |
| Drain-Source Diode Characteristics | I                   |   |     |      |      |      |
| Diode Forward Voltage (Note 3)     | V <sub>SD</sub>     | V <sub>GS</sub> =0V,I <sub>S</sub> =4A                  | -   | -    | 1.2  | V    |
| Diode Forward Current (Note 2)     | ls                  |   | -   | -    | 4    | Α    |

## Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.

2. The value of R θJA is measured with the device mounted on 1in 2 FR-4 board with 2oz. Copper, in a still air environment with T <sub>A</sub>=25°C. The value in any given application depends on the user's specific board design.

**3.** Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

4. Guaranteed by design, not subject to production

5. EAS condition : Tj=25  $^\circ C$  ,V\_{DD}=30V,V\_G=10V,L=0.5mH,Rg=25\Omega



## **Typical Electrical and Thermal Characteristics**



Figure 1:Switching Test Circuit











V<sub>GS</sub>=10V

30

20 10



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# NCE6004





Figure 8 Drain-Source On-Resistance





0.6

0.8

1.0

1.2

1.4

0.0

0.2

0.4



100



Figure 14 Normalized Maximum Transient Thermal Impedance



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# NCE6004

# **SOT-23 Package Information**











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